# **Energy-Resolved Quadrupole Mass Spectrometry in II<sup>B</sup>-VI<sup>A</sup> Sputtering Investigations**

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### **Sputtering Studies Useful but not Common**

- Sputtering is often treated as a black box
  - Control inputs: power, pressure, ambient composition, etc.
- Observe film properties: crystallinity, transmittance, conductivity, etc. • This approach does not consider complex sputtering phenomena
  - Ion/electron energy
  - Particle aggregation/film nucleation



#### Use mass spectrometry to advance understanding

- Chemistry/composition of sputtered particles
- Critical energetics/potentials

# **Equipment: QMS Mounted to Sputtering Chamber**

- The Sputter-Plasma Diagnostic (SPD) multi-source UHV chamber
- Hiden EQP 500 Quadrupole Mass Spectrometer
  - Mounted via rotating flange with 2-axis motion
  - Line of sight access to sputtering plasma
  - Capable of analyzing neutrals and plasma-generated ions



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# Identification of ZnS Mass Spectra

- Do particles sputter atomically or in clusters?
- RF magnetron sputtered ZnS in pure Ar ambient





- Atomic ions more prevalent than clusters
- Ion fluxes: Ar > Zn > S > ZnAr > ZnS

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# Sputtered II<sup>B</sup>-VI<sup>A</sup> Materials Used in Thin Film PV





# **ZnS Ion Energy Distribution (IED) Scans**

- Peak position equal to plasma potential<sup>1</sup>
- Electron temperature fro
- Experimental design
  - Sputter ZnS in Ar ambient



- Uncertainty in peak position ~0.5 eV
  - Bimodal IED for Ar, single mode for Zn and S

  - Increasing potential with increasing power

• Plot of Intensity vs. arrival energy of plasma-generated ions

$$\sum_{p \to W_{f}} V_{p} - V_{f} = \frac{T_{e}}{2e} \left[ 1 + \ln \left( \frac{m_{i}}{2\pi m_{e}} \right) \right]$$

• Investigate reproducibility, effects of flight distance, pressure, and power • Baseline conditions: 26 cm displacement, 5 mTorr, 30 W



• Scans show good reproducibility; plasma potential is highly variable

• Near-linear decrease in potential with increasing distance from target • Exponential drop in potential with increasing pressure

#### Conclusions

• Under baseline conditions, atomic sputtering dominates • Processing conditions greatly affect arrival energy of sputtered ions

#### **Future work**

 Investigate oxygen incorporation in CdS and ZnS films • Identify process conditions for atomic vs. cluster sputtering

#### References

<sup>1</sup>K. Ellmer, T. Welzel, Reactive magnetron sputtering of transparent conductive oxide thin films: Role of energetic particle (ion) bombardment, J. Mater. Res. 27 (2012), 765.

